

**REMARKS**

Claims 1-3 and 6-20 are now pending in the present application. Claims 1 and 5-19 are rejected. Claim 5 is herein canceled. Claim 1 is herein amended. New claim 20 is herein added. No new matter has been presented.

**Rejections under 35 U.S.C. §103(a)**

Claims 1,2, 3, 5, 6, 8, 11, 12 , 14, 17 and 18 are rejected under 35 U.S.C. §103(a) as being unpatentable over Wong (US Patent 5,423,944) in view of Dobuzinsky et al. (US Patent 5,412,246) and Murakawa et al. (US200710085154).

Claims 7, 9, 13, 15 and 16 are rejected under 35 U.S.C. §103(a) as being unpatentable over Wong in view of Dobuzinsky et al. and Murakawa et al. as applied to claim 3 above, and further in view of Muramatsu et al. (US Patent 6,468,841). The Examiner admits that Wong, Dobuzinsky et al. and Murakawa et al. disclose the forming of two insulation layers, but fail to teach the use of nitric acid and an ozone containing solution. The Examiner asserts that Muramatsu disclose the use of nitric acid and an ozone containing solution at temperature of 420 degrees C. The Examiner concludes that it would have been obvious to combine the teachings of Wong and Dobuzinsky et al. and Murakawa et al. in view of Muramatsu et al. because the oxidizing agents such as nitric acid help remove defects and the radial slot line antenna will form a high quality film at low temperatures with fewer dangling bonds.

Applicants herein amend the claims to clarify the invention. Thereafter, Applicants respectfully disagree with the rejections because the cited references, alone or in combination, fail to teach or suggest all of the claimed limitations.

The present invention, as herein clarified, is a SONOS transistor. This is noted in the specification on page 7, lines 6-28.

Specifically, the present application discloses the SONOS transistor composed of a semiconductor substrate 1 (S), a tunnel oxide film 15a (O) corresponding to the first oxide film, a silicon nitride film 15c (N), a silicon oxide film 15d (O) corresponding to the second oxide film and a polycrystalline silicon film 18 (S) corresponding to the semiconductor film, as in Fig. 6B.

Applicants note that the processing for the formation of a film at low-temperature recited in claim 1 is performed for the tunnel oxide film 15a in the SONOS transistor.

Applicants submit that none of Wong, Dobuzinsky et al. and Murakawa et al., alone or in combination, discloses or suggests a SONOS transistor construction recited in claim 1.

New claim 20 indicates the present application can be applied to an embedded-bit-line-type SONOS transistor, and is described in the specification on page 7, lines 6-28. Applicants note that none of Wong, Dobuzinsky et al. and Murakawa et al., alone or in combination, teaches or fairly suggest an embedded-bit-line-type SONOS transistor.

In view of the aforementioned amendments and accompanying remarks, Applicants submit that the claims, as herein amended, are in condition for allowance. Applicants request such action at an early date.

Application No. 10/659,748  
Attorney Docket No. 031140

Amendment under 37 C.F.R. §1.116  
Amendment filed August 12, 2008

If the Examiner believes that this application is not now in condition for allowance, the Examiner is requested to contact Applicants' undersigned attorney to arrange for an interview to expedite the disposition of this case.

If this paper is not timely filed, Applicants respectfully petition for an appropriate extension of time. The fees for such an extension or any other fees that may be due with respect to this paper may be charged to Deposit Account No. 50-2866.

Respectfully submitted,

**WESTERMAN, HATTORI, DANIELS & ADRIAN, LLP**



Kenneth H. Salen  
Attorney for Applicants  
Registration No. 43,077  
Telephone: (202) 822-1100  
Facsimile: (202) 822-1111

KHS/klf